A new EM-material comprised of nano-composite ferromagnetic oxide films

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We have reported that nano-composite ferromagnetic oxide films with the Bi_2O_3 - Fe_2O_3 - $PbTiO_3$ system prepared by rf-reactive sputtering exhibit ferromagnetism and ferroelectricity above room temperature^(1,2). We found that these films show a kind of electromagnetic (EM-) effect, ie. the electric polarization ΔP is induced by applying magnetic field H. An example of the experimental results is shown in the left side figures for a film with $0.18Bi_2O_3$ - $0.7Fe_2O_3$ - $0.12PbTiO_3$ after post-annealing at 650°C for 3h in air. The top figure is the magnetization curve, the middle one is the relative change of the dielectric permeability $\Delta \varepsilon_r$ '/ ε_r ' by H, and the bottom one is ΔP induced by H, where an ac tickle

field $h(\omega)$ was applied simultaneously normal to the film plane. These experimental results are qualitatively explained by a model based on magnetization rotation of ferromagnetic nano-clusters randomly dispersed and embedded in the ferroelectric glassy matrix. The calculated results are drawn in the right side figures. The key-factors to determine ΔP are summarized as: $^{(3,4)}$

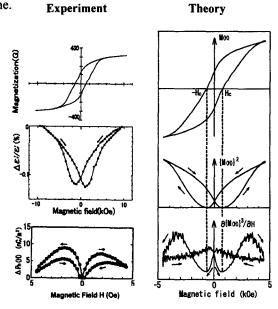
$$\Delta P_{\rm E}({\rm H}) \propto \Delta \varepsilon_{\rm r}' / \varepsilon_{\rm r}' \propto [{\rm M}({\rm H})]^2$$

$$\Delta P_h(H) \propto \partial / \partial H[M(H)]^3$$
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In calculation, we used the measured magnetization M(H) (the top figure) was used.

References

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